Form PTO-1449	OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use Several Sheets if Necessary)	ATTY. DOCKET NO. JG001[redacted]	SERIAL NO.
		Yu et al.	
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REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER							ISSUE DATE	NAME	CLASS	SUBCLASS	FILING DATE
SAL	A	4	5	2	3	2	1	1	6/11/85	Morimoto et al.	357	4	3/8/83
	B	5	4	7	8	6	5	3	12/26/96	Guenzer	428	446	4/4/94
	AA	3	8	0	2	9	6	7	4/9/74	Landany et al.	148	171	8/27/91
	AB	4	4	0	4	2	6	5	9/13/83	Manasevit	428	689	4/7/78
	AC	4	4	8	2	9	0	6	11/13/84	Hovel et al.	357	16	6/30/82
	AD	4	8	4	6	9	2	6	7/11/89	Kay et al.	156	612	9/3/87
	AE	4	8	8	2	3	0	0	11/21/89	Inoue et al.	437	236	10/6/88
	AF	4	8	9	1	0	9	1	1/2/90	Shastry	156	606	6/8/87
	AG	4	9	2	8	1	5	4	5/22/90	Umeno et al.	357	16	3/20/89
	AH	4	9	6	3	9	4	9	10/16/90	Wanlass et al.	357	16	9/30/88
	AI	4	9	9	9	8	4	2	3/12/91	Huang et al.	372	45	3/1/89
	AJ	5	1	4	1	8	9	4	8/25/92	Bisaro et al.	437	132	7/20/90
	AK	5	1	5	5	6	5	8	10/13/92	Inam et al.	361	321	3/5/92
	AL	5	1	5	9	4	1	3	10/27/92	Calviello et al.	505	1	12/11/90
	AM	5	2	2	1	3	6	7	6/22/93	Chisholm et al.	148	33	8/3/88
	AN	5	2	2	5	0	3	1	7/6/93	McKee et al.	156	612	4/10/91
	AO	5	2	4	8	5	6	4	9/28/93	Ramesh	428	688	12/9/92
	AP	5	2	7	0	2	9	8	12/14-93	Ramesh	505	1	8/4/92
	AQ	5	3	1	0	7	0	7	5/10/94	Oishi et al.	501	126	9/28/92
	AR	5	3	2	6	7	2	1	7/5/94	Summerfelt	437	131	5/1/92
	AS	5	4	1	8	3	8	9	5/23/95	Watanabe	257	295	11/9/93
	AT	5	5	5	6	4	6	3	9/17/96	Guenzer	117	90	6/5/95
	AU	5	6	7	0	7	9	8	9/23/97	Schetzina	257	96	3/29/95
	AV	5	6	7	4	3	6	6	10/7/97	Hayashi et al.	204	298.09	6/7/95
	AW	5	7	3	1	2	2	0	3/24/98	Tsu et al.	437	60	6/7/95
	AX	5	7	3	5	9	4	9	4/7/98	Mantl et al.	117	8	4/7/98
	AY	5	7	4	1	7	2	4	4/21/98	Ramdani et al.	437	128	12/27/96
	AZ	5	8	0	1	1	0	5	9/1/98	Yano et al.	438	785	6/14/96
	BA	5	8	1	0	9	2	3	9/22/98	Yano et al.	117	84	5/10/96
	BB	5	8	2	8	0	8	0	10/27/98	Yano et al.	257	43	8/17/95
	BC	5	8	7	4	8	6	0	2/23/99	Brunel et al.	330	285	12/4/96
	BD	6	0	0	2	3	7	5	12/14/99	Corman et al.	343	853	9/2/97
	BE	6	0	4	5	6	2	6	4/4/00	Yano et al.	148	33.4	6/23/98
	BF	6	0	5	5	1	7	9	4/25/00	Koganei et al.	365	158	5/17/99
	BG	6	0	6	4	0	7	8	5/16/00	Northrup et al.	257	96	5/22/98
	BH	6	1	0	3	0	0	8	8/15/00	McKee et al.	117	2	7/30/98
	BI	6	1	0	7	6	5	3	8/22/00	Fitzgerald	257	191	6/23/98
	BJ	6	1	1	3	6	9	0	9/5/00	Yu et al.	117	84	6/8/98
	BK	6	1	4	3	0	7	2	11/7/00	McKee et al.	117	08	4/6/99

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SH	EN	5	9	1	2	0	6	8	6/15/99	Jia	428	210	12/5/96
	EO	5	8	3	0	2	7	0	11/3/98	McKee et al.	117	106	8/5/96
	EP	5	5	8	8	9	9	5	12/31/96	Sheldon	117	201	5/3/95
	EQ	5	5	1	4	4	8	4	5/7/96	Nashimoto	428	700	10/19/93
	ER	5	4	8	2	0	0	3	1/9/96	McKee et al.	117	108	7/6/93
	ET	5	4	5	0	8	1	2	9/19/95	McKee et al.	117	84	12/8/93
	EU	5	4	1	8	2	1	6	5/23/95	Fork	505	473	5/15/92
	EV	5	3	9	3	3	5	2	2/28/95	Summerfelt	148	33.3	9/27/93
	EW	5	3	5	8	9	2	5	10/25/94	Neville Connell et al.	505	235	8/10/92
	EX	5	1	7	3	4	7	4	12/22/92	Connell et al.	505	1	3/11/91
	EY	4	9	1	2	0	8	7	3/27/90	Aslam et al.	505	1	4/15/88
	EZ	4	6	6	1	1	7	6	4/28/87	Manasevit	148	175	2/27/85

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FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER								GRANT DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES	TRANSLATION NO
SLL	BL	0	2	5	0	1	7	1	11/11/92	EPC			X	
	BM	0	3	4	2	9	3	7	11/23/89	EPC			X	
	BN	0	4	5	5	5	2	6	6/11/91	EPC			X	
	BO	0	6	0	2	5	6	8	6/22/94	EPC			X	
	BP	0	6	0	7	4	3	5	7/27/94	EPC			X	
	BQ	1	0	0	1	4	6	8	5/17/00	EPC			X	
	BR	0	5	1	4	0	1	8	11/19/92	EPC			X	
	BT	0	9	9	9	6	0	0	5/10/00	EPC			X	
	BU	1	3	1	9	3	1	1	6/6/73	Great Britain			X	
	BV	6	2	9	1	2	9	9	10/18/94	Japan			X	
	BW	1	1	2	3	8	6	8	8/31/99	Japan			X	
	BX	1	1	2	6	0	8	3	9/24/99	Japan			X	
	BY	2	0	0	0	0	3	9	1/5/90	Japan			X	
	BZ	5	0	4	8	0	7	2	2/26/93	Japan			X	
	CA	5	2	0	8	8	3	5	7/23/77	Japan			X	
	CB	5	4	1	3	4	5	5	10/19/79	Japan			X	
	CC	5	5	0	8	7	4	2	7/2/80	Japan			X	
	CD	6	1	1	0	8	1	8	5/26/86	Japan			X	
	CE	6	2	3	2	1	2	6	8/19//94	Japan			X	
	CG	6	3	0	3	4	9	9	2/15/88	Japan			X	
	CI	6	3	1	3	1	1	0	6/3/88	Japan			X	
	CH	6	3	1	9	8	3	6	8/17/88	Japan			X	
	CK	6	3	3	4	1	6	8	6/14/93	Japan			X	
	CK	9	9	1	4	8	0	4	3/25/99	PCT			X	
✓	CL	9	9	6	3	5	8	0	12/9/99	PCT			X	

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Form PTO-1449	LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use Several Sheets if Necessary)	ATTY. [redacted]ET NO. JG00143	SERIAL NO.
		FILING DATE	GROUP

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	CN	"Integration of GaAs on Si using a spinel buffer layer, IBM Technical Bulletin," vol. 30, no. 6, Nov. 1987, p. 365
	CM	"GaInAs Superconducting FET," IBM Technical Bulletin, vol. 36, no. 8, Aug. 1993, p. 655.
	CO	"Epitaxial 3d Structure Using Mixed Spinel," IBM Technical Bulletin, vol. 30, no. 3, Aug. 1987, p. 1271.
	CP	"Roles of Buffer Layers in Epitaxial Growth of $SrTiO_3$ Films on Silicon Substrates,"Moon et al., Japan J of Appl Phys., vol. 33, 1994. pp 1472-1477.
	CQ	"GaAs Heteroepitaxial Growth on Si Substrates with Thin Si Interlayers in Situ Annealed at High Temperatures," Yodo et al., 8257b Journal of Vacuum Science & Technology, 1995, no. 3, pp. 1000-1005.
	CR	"Substrate Effect on the Superconductivity of $Yba_2Cu_3O_7$ Thin Films," Cuomo et al., AIP conference 1988, pp. 141-148.
	CS	"Crystalline Oxides on Silicon: The First Five Monolayers,", McKee et al., Physical Review Letters, vol. 81, no. 14, Oct. 1998, pp. 3014-3017.
	CT	"Molecular Beam Epitaxy Growth of Epitaxial Barium Silicide, Barium Oxide, and Barium Titanate on Silicon," McKee et al., 1991 American Institute of Physics, pp. 782-284.
	CU	"Molecular Beam Epitaxy Growth of $SrTiO_3$ Films on Si(100)-2 x 1 with SrO Buffer Layer," Tambo et al., Jpn. J. Appl. Phys., vol 37, 1998 pp. 4454-4459.
	CV	"The MBE Growth and Optical Quality of $BaTiO_3$ and $SrTiO_3$ Thin Films on MgO," McKee et al,. Mat. Res. Soc. Symp. Proc. Vol. 341, 1994, pp. 309-314.
	CW	"$BaSi_2$ and Thin Film Alkaline Earth Silicides on Silicon," McKee et al., Appl. Phys. Lett. 63 (20), Nov. 1993, pp. 2818-2820.
	CX	"Surface Structures and the Orthorhombic Transformation of Thin Film $BaSi_2$ on Silicon," McKee et al., Mat. Res. Soc. Symp. Proc. Vol. 221, pp. 131-136.
	CY	"Epitaxial Growth of of $SrTiO_3$ Films on Si(100) Substrates Using a Focused Electron Beam Evaporation Method," Mori et al. Jpn. J. of Appl. Phys., vol. 30, no. 8a, Aug. 1991, pp. 1415-1417.
	CZ	"Growth of Crystalline $SrTiO_3$ Films on Si Substrates Using Thin Fluoride Buffer Layers and Their Electrical Properties," Moon et al., Jpn. J. of Apl. Phys., vol. 33, (1994), pp. 5911-5916.
	DA	"The Epitactic Growth of Oxides on Si," S. Summerfelt, Materials Research Society Symposium Proceedings, vol. 221, 1991, pp. 29-34

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Form PTO-1449	[redacted] OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use Several Sheets if Necessary)	ATTY. [redacted] KET NO. JG0014[redacted]	SERIAL NO.
		FILING DATE	GROUP

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	DB	"Oriented Growth of $SrTiO_3$ Films on Si(100) Substrates Using in situ Cleaning by Excited Hydrogen," H. Ishiwara et al., Mat. Res. Soc. Symp., vol. 116, 1988., pp. 369-374
	DC	"A Preliminary Consideration of the Growth Behavior of CeO_2, $SrTiO_3$ and $SrVO_3$ Films on Si Substrate," Nagata et al., Thin Solid Films, 224, 1993, pp. 1-3.
	DD	"Heteroepitaxial Growth of CeO_2(001) Films on Si(001) Substrates by Pulsed Laser Deposition in Ultrahigh Vacuum," Nagata et al., Jpn. J. Appl. Phys., vol. 30, no. 6b, 1991, pp. 1136-1138.
	DE	"Heteroepitaxial Growth of SrO Films on Si Substrates," Kado et al., J. Appl. Phys., 61(6), 1987, pp. 2398-2400.
	DF	"Epitaxial Growth of Perovskite Type Oxide Films on Si Substrates," H. Ishiwara et al., Mat. Res. Soc. Symp., vol. 220, 1991, pp. 595-600.
	DG	"Effects of Buffer Layers in Epitaxial Growth of $SrTiO_3$ Thin Film on Si(100)," Nakagawara et al., J. Appl. Phys. 78(12), 1995, pp.7226-7230.
	DH	"A Proposal of Epitaxial Oxide Thin Film Structures for Future Oxide Electronics," Suzuki et al., Materials Science and Engineering B41 (1996), pp. 166-173.

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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	DI	"Optimizing GMR Spin Valves: The Outlook for Improved Properties", W. F. Englhoff et al., 1998 Int'l NonVolatile Memory Technology Conference, pp. 34-37.
	DJ	"Processing and Performance of Piezoelectric Films", Y. Wang et al. , Univ. of MD, Wilcoxon Research Co., and Motorola Labs.
	DK	"Nonlinear acoustoelectric interactions in GaAs/$LiNbO_3$ structures", M. Rotter et al., 1999 American Institute of Physics, pp. 965-967.
	DL	"Surface acoustic wave propagation on lead zirconate titanate thin films", K. Sreenivas et al., App. Phys. Lett. 52(9), 29 February 1988, pp. 709-711.
	DM	"Single Chip fused hybrids for acousto-electric and acousto-optic applications", M. Rotter et al., 1997 American Institute of Physics, pp. 2097-2099.
	DN	"Surface Acoustic Wave Propagation in PZT/YBCO/$SrTiO_3$ and PbTi O_3/YBCO/$SrTiO_3$ Epitaxial Heterostructures", Dept. of Physics & Astrophysics, Univ. of Delhi, pp. 275-283.
	DO	"Ferroelectric Field Effect Transisitor Based on Epitaxial Perovskite Heterostructures", S. Mathews et al., American Association for the Advancement of Science, 1997, pp.238-240.
	DP	"Formation of Si Epi./Mg0-$Al_2 0_3$ Epi./$Si0_3$/Si and Its Epitaxial Film Quality," Masao Mikami et al., Fundamental Research Laboratories and Microelectronics Laboratories, pp. 31-34.
	DQ	"An Epitaxial Si/Insulator/Si Structure Prepared by Vacuum Deposition of CaF_2 and Silicon," T. Asano et al., Graduate School of Science and Engineering, Tokyo Institute of Technology, pp. 143-151.
	DR	"Reaction and Regrowth Control of $Ce0_2$ on Si(111) Surface for the Silicon-On-Insulator Structure," T. Chikyow et al., Appl. Phys. Lett. 65(8), 22 August 1994, pp. 1030-1032.
	DS	"Epitaxial Growth of $Ce0_2$(100) Films on Si(100) Substrates by Dual Ion Beams Reactive Sputtering," J.F. Kang et al., Solid State Communications, Vol. 108, No. 4, pp. 225-227.
	DT	"Vertical-Cavity Surface-Emitting Lasers Come of Age," Robert A. Morgan et al., SPIE, Vol. 2683, pp. 18-29.
	DU	"Technical Analysis of Qualcomm QCP-800 Portable Cellular Phone(Transmitter Circuitry)," Talus Corporation, Qualcomm QCP-800 Technical Analysis Report, December 10, 1996, pp. 5-8.
	DV	"Properties of GaAs Si Grown by Molecular Beam Epitaxy,"R. Houdre et al., Solid State and Molecular Sciences, 1990, pp. 91-114.
	DW	"Gallium Arsenide and Other Compound Semiconductors on Silicon," S.F. Fang et al., J. Appl. Phys. 68(7), 1 October 1990, pp. R31-R58.

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		FILING DATE	GROUP

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	DX	"Impact of GaAs Buffer Thickness on electronic Quality of GaAs Grown on Graded Ge/GeSi/Si Substrates," Carlin et al., Appl. Phys. Letter, vol. 76, no. 14, April 2000, pp. 1884-1886.
	DY	"Epitaxial Integration of III-V Materials and Devices with Si Using Graded GeSi Buffers," Ringel et al., 27th International Symposium on Compound Semiconductors, Oct. 2000.
	DZ	"Progess in Compound-Semiconductor-on-Silicon-Heteroepitaxy with Fluoride Buffer Layers," Zogg et al., J. Electrochem Soc., vol. 136, no. 3, March 1989, pp. 775-779.
	EA	"Oxide Defined GaAs Vertical-Cavity Surface-Emitting Lasers on Si Substrates," Xiong et al., IEEE Photonics Tech Letters, vol. 12, no. 2, Feb 2000, pp. 110-112.
	EB	"Investigation of PZT/?LSCO/Pt//Aerogel Thin Film Composites for Uncooled Pyroelectric IR Detectors," Clem et al., Mat. Res. Soc. Symp. Vol. 541, pg. 661-666.
	EC	"Bound-To-Quasi-Bound Quantum-Well Infrared Photodetectors," Gunapala et al., NASA Tech Brief, vol. 22, no. 9.
	ED	"Monolithic InGaAs-on-silicon Short Wave Infrared Detector Arrays," Joshi et al., Int'l. Society for Optical Engineering, vol. 2999, pp. 211-224.
	EE	"Nanostructure and Chemistry of a (100)Mg)/(100)GaAs Interface," Bruley et al., Appl. Phys Lett. 65(5), Aug. 1994, pp.564-566.
	EF	"Epitaxial MgO on Si(001) for Y-Ba-Cu-O Thin Film Growth by Pulsed Laser Deposition," Fork et al., Appl. Phys Lett 58(20), May 1991, pp. 2294-2296.
	EG	"Dialectrics on Semiconductors," Himpsel et al., Materials Science and Engineering, B1(1988), pp. 9-13.
	EH	"Epitaxial La 0.67 Sr 0.33 MnO_3 Magnetic Tunnel Junctions," J. Appl. Phys. 81(8), Apr. 1997 pp. 5509-5511
	EI	"Colossal Magnetoresistance Magnetic Tunnel Junctions Grown by Molecular-Beam Epitaxy," O'Donnell et al., Appl. Physics Letters, bol. 76, no. 14, Apr. 2000, pp. 1914-1916.

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